

Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5347-208		Serial No. 09/891,552	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Gerald Lucovsky et al.			
				Filing Date: June 25, 2001		GAU: 28145	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
DEC 09 2002 a.u. PATENT & TRADEMARK OFFICE		1 Wilk et al., <i>High-K Gate Dielectrics: Current Status and Materials Properties Considerations</i> , Journal of Applied Physics, Vol. 89, No. 10, May 15, 2001, pp. 5243-5275					
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Examiner:

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